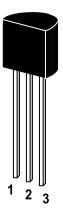


## **NPN Silicon Epitaxial Planar Transistor**

for switching and AF amplifier applications.

The transistor is subdivided into six groups, D, E, F, G, H and I, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Base 3. Collector

TO-92 Plastic Package Weight approx. 0.19g

## Absolute Maximum Ratings ( $T_a = 25^{\circ}C$ )

	Symbol	Value	Unit
Collector Base Voltage	V <sub>CBO</sub>	30	V
Collector Emitter Voltage	V <sub>CEO</sub>	20	V
Emitter Base Voltage	V <sub>EBO</sub>	4	V
Collector Current	Ic	25	mA
Power Dissipation	P <sub>tot</sub>	400	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	Ts	-65 to +150	°C









## Characteristics at T<sub>amb</sub>=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at $V_{CE}$ =5 $V$ , $I_{C}$ =1 $mA$					
Current Gain Group D	$h_{FE}$	28	-	45	-
E	$h_{FE}$	39	-	60	-
F	$h_{FE}$	54	-	80	-
G	$h_{FE}$	72	-	108	-
н	$h_{FE}$	97	-	146	-
1	$h_{FE}$	132	-	198	-
Collector Base Breakdown Voltage					
at I <sub>C</sub> =100μA	$V_{(BR)CBO}$	30	-	-	V
Collector Emitter Breakdown Voltage					
at I <sub>C</sub> =1mA	$V_{(BR)CEO}$	20	-	-	V
Emitter Base Breakdown Voltage					
at I <sub>E</sub> =100μA	$V_{(BR)EBO}$	4	-	-	V
Collector Cutoff Current					
at V <sub>CB</sub> =30V	$I_{CBO}$	-	-	100	nA
Emitter Cutoff Current					
at V <sub>EB</sub> =3V	I <sub>EBO</sub>	-	-	100	nA
Collector Emitter Saturation Voltage					
at I <sub>C</sub> =10mA, I <sub>B</sub> =1mA	$V_{CE(sat)}$	-	0.1	0.3	V
Base Emitter on Voltage					
at $V_{CE}$ =5V, $I_C$ =1mA	$V_{BE(on)}$	-	0.72	-	V
Collector Base Capacitance					
at V <sub>CB</sub> =10V, f=1MHz	$C_{CBO}$	-	1.2	1.6	pF
Gain Bandwidth Product					
at $V_{CE}$ =5V, $I_{C}$ =1mA	f⊤	400	620	-	MHz







